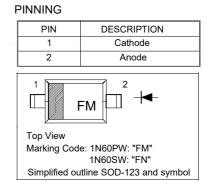
1N60PW, 1N60SW Schottky Barrier Diode

FEATURES

- · High reliability
- · Low forward voltage and reverse current

APPLICATIONS

- For electronic calculator, etc.
- Low current rectification and high speed switching



Parameter	Symbol	Value	Unit	
Peak Reverse Voltage	Vrm	45	V	
Reverse Voltage	V _R	10	V	
Peak Forward Current	Іғм	150	mA	
Average Rectified Output Current	lo	50	mA	
Surge Forward Current	Isurge	500	mA	
Junction Temperature	ТJ	125	S₀	
Storage Temperature Range	Tstg	-55 to +125	٥C	

Absolute Maximum Ratings (T_a = 25_°C)

Characteristics (T_a = 25 °C)

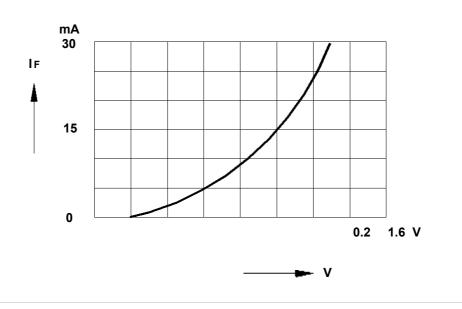
Parameter	Symbol	Min.	Max.	Unit
Forward Current at $V_F = 1 V$	l _F	4	-	mA
Reverse Current at V _R = 10 V 1N60PW 1N60SW	lĸ	-	50 100	μA
Reverse Voltage at I _R = 100 μA	V R	45	-	V
Junction Capacitance at f = 1 MHz, V = -1 V	CJ	-	1	pF
Rectification efficiency at Vi = 2 Vrms, R = 5 K Ω , C = 20 pF, f = 40 MHz	η	55	-	%

Pair Δ I_F ≤ 6 mA at 1V, Δ I_R ≤ 20 µA at 10 V

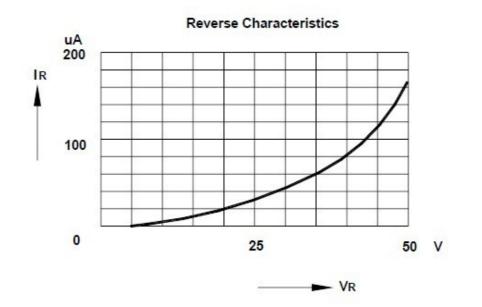




Typical Characteristics



Forward Characteristics





PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

